

Amendments to the Claims:

1-12. (canceled)

5 13. (currently amended) A heterojunction bipolar transistor, comprising:

a collector region;

a SiGe base region;

an emitter stack overlaying said collector region, said emitter stack including an emitter opening filled with T-shaped polysilicon, said T-shaped polysilicon overlaying
 10 nitride regions included in said stack, **and said emitter stack including an implant-
 masking cap layer on top of said T-shaped polysilicon, and wherein said emitter
 stack does not have spacers;** and

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 one and another extrinsic base regions arranged on respective sides of said emitter stack, said extrinsic base regions being directly aligned with said emitter polysilicon
 15 region but not being directly aligned with said emitter opening.

14. (original) The transistor of claim 13, wherein said extrinsic base regions are made from SiGe polysilicon.

20 15. (previously amended) The transistor of claim 13, wherein said one of said extrinsic base regions is longer than said another of said extrinsic base regions, and wherein a base contact is formed on the longer extrinsic base region.

16. (currently amended) The transistor of claim 13, wherein said ~~reach-through~~ collector
 25 region, emitter stack, and extrinsic base regions are contacted using mid-end-of-line collector, emitter, and base ~~contact~~ contacts respectively.